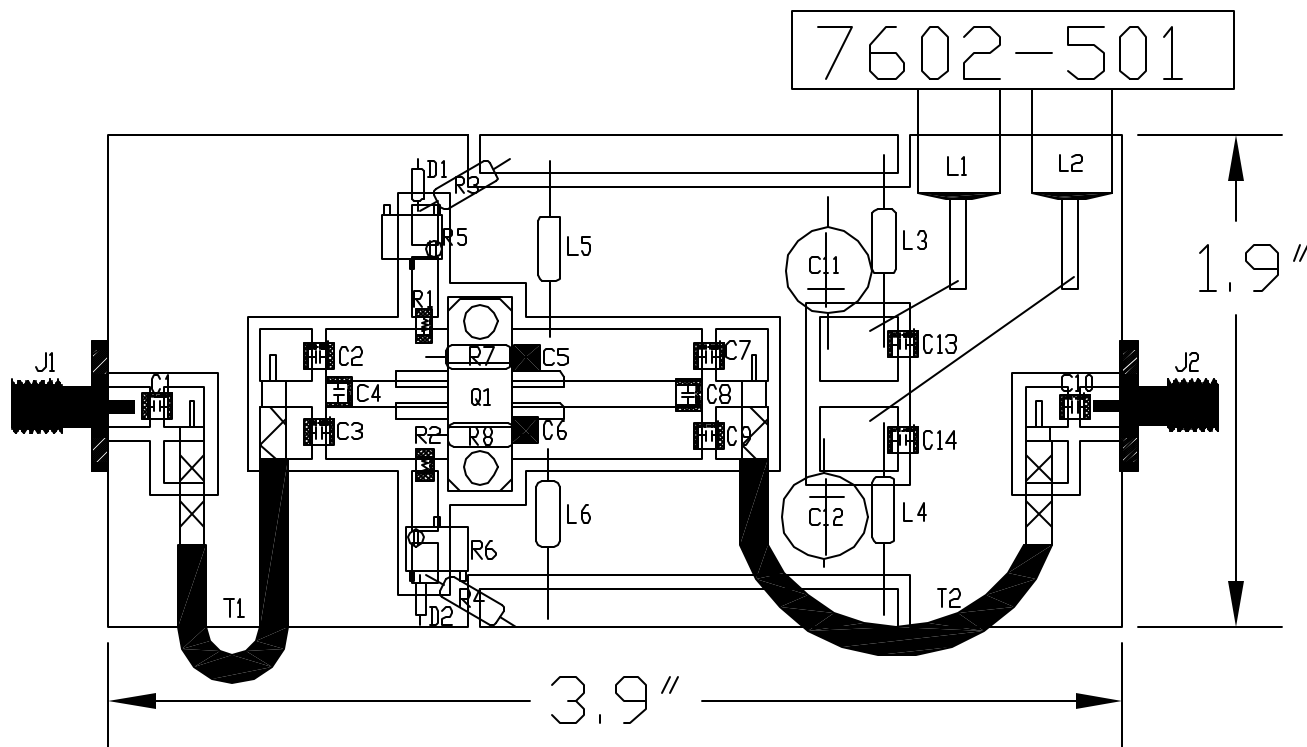
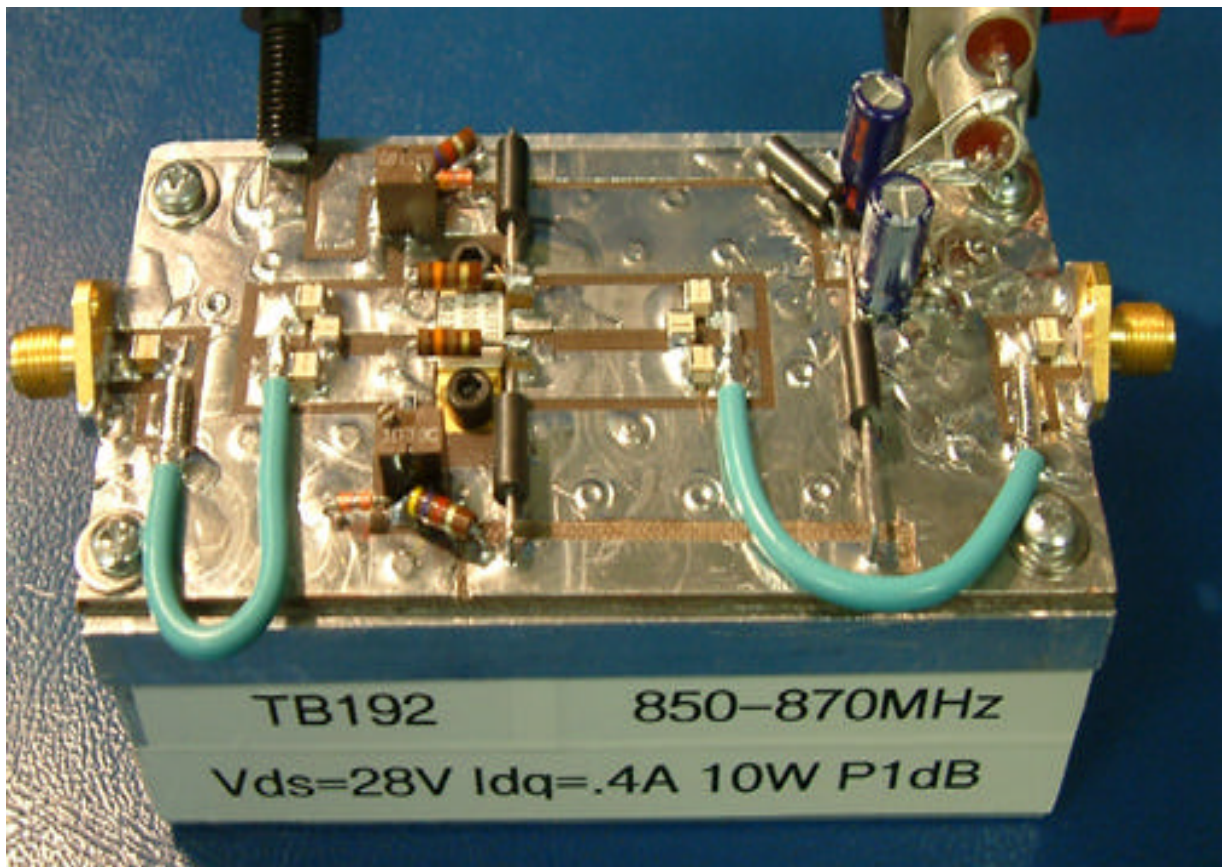


Title		
TB192, SQ202, 850MHz-870MHz, Gain=10dB, 10W P1dB		
Size	Document Number	Rev
A	Vds=28V Idq=.4A Resistance in Ohms, Capacitance in Farads	
Date:	Tuesday, October 05, 2004	Sheet 1 of 1



SYMBOL	VALUE	DESCRIPTION
C1	1.5pF	ATC100B Capacitor
C2, C3, C7, C9	120pF	ATC100B Capacitor
C4	7.5pF	ATC100B Capacitor
C5, C6, C13, C14	.01uF	ATC200B Capacitor
C8	3.9pF	ATC100B Capacitor
C10	33pF	ATC100B Capacitor
C11, C12	47uF	63V Aluminum Electrolytic
D1, D2	6.8V	Axial Zener Diodes 20mA
J1, J2	---	SMA-Female Connector
L1, L2	---	Tusorix EMI Filter 7602-501
L3, L4, L5, L6	850nH	Axial RF Choke
J1, J2	---	SMA Connector
R1, R2	10K Ohms	1206 SM Resistor
R3, R4	4.7K Ohms	1/4 W Axial Resistor
R5, R6	10K-Ohm	6m PWT, 31gkey p/n ST5V102CT-ND
R7, R8	130 Ohms	1/4 W Axial Resistor
T1, T2	50-Ohm	Micro-Coax UT-DBSC-FURN-F
Q1	SQ202	Polyfet Transistor
Vds	28V	Drain-to-Source Voltage
Idq	.4A	Quiescent Drain Current

DRN BY: TChang	10/16/2004	POLYFET RF DEVICES	
CHKD : JCitrolo	10/16/2004		
ELECT :		TB192 850-870MHz Gain=10dB 10W P1dB	
MECH :		SIZE	FSCM NO
PRDC :		PCB LAYOUT	
QUAL :			REV 1
PGMS :		SCALE : 1 : 1	SHEET 1 OF 1



TB192

850-870MHz

Vds=28V Idq=.4A 10W P1dB